

**General Description**

The AO4938 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in DC-DC converters. A monolithically integrated Schottky diode in parallel with the synchronous MOSFET to boost efficiency further.

**Product Summary**
**FET1(N-Channel)**

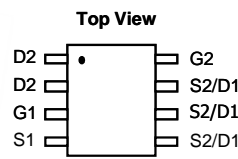
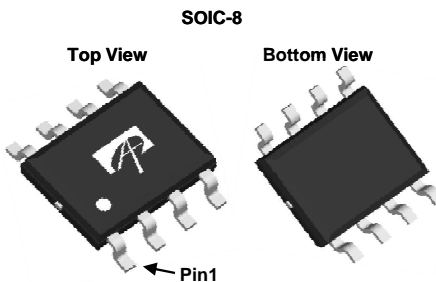
$V_{DS} = 30V$   
 $I_D = 8.8A$  ( $V_{GS}=10V$ )  
 $R_{DS(ON)} < 16m\Omega$  ( $V_{GS}=10V$ )  
 $< 22m\Omega$  ( $V_{GS}=4.5V$ )

**FET2(N-Channel)**

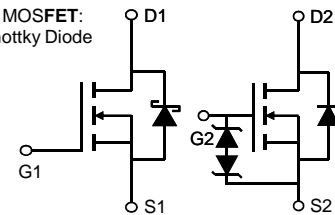
$30V$   
 $8A$  ( $V_{GS}=10V$ )  
 $R_{DS(ON)} < 19m\Omega$  ( $V_{GS}=10V$ )  
 $< 28m\Omega$  ( $V_{GS}=4.5V$ )

100% UIS Tested  
 100%  $R_g$  Tested

ESD Protected  
 100% UIS Tested  
 100%  $R_g$  Tested



**SRFET™**  
 Soft Recovery MOSFET:  
 Integrated Schottky Diode


**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Max FET1	Max FET2	Units
Drain-Source Voltage	$V_{DS}$	30	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_A=25^\circ C$	8.8	A
		$T_A=70^\circ C$	7.1	
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	60	40	A
Avalanche Current <sup>C</sup>	$I_{AS}, I_{AR}$	21	13	A
Avalanche energy $L=0.3mH$ <sup>C</sup>	$E_{AS}, E_{AR}$	66	25	mJ
Power Dissipation <sup>B</sup>	$P_D$	$T_A=25^\circ C$	2	W
		$T_A=70^\circ C$	1.3	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150		$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A,D</sup>		Steady-State	74	90
Maximum Junction-to-Lead	$R_{\theta JL}$	32	40	$^\circ C/W$

**FET1 Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250uA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V T <sub>J</sub> =125°C			0.1 20	mA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.1	1.65	2.2	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	60			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =8.8A T <sub>J</sub> =125°C		13.3 20	16 25	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =7A		18	22	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =8.8A		29		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.41	0.5	V
I <sub>S</sub>	Maximum Body-Diode + Schottky Continuous Current				3.5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		1267	1600	pF
C <sub>oss</sub>	Output Capacitance			308		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			118		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		1.3	2.0	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =8.8A		21	30	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			10.4		nC
Q <sub>gs</sub>	Gate Source Charge			3		nC
Q <sub>gd</sub>	Gate Drain Charge			3.6		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.7Ω, R <sub>GEN</sub> =3Ω		5.2		ns
t <sub>r</sub>	Turn-On Rise Time			3.8		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			21.2		ns
t <sub>f</sub>	Turn-Off Fall Time			4.4		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =8.8A, di/dt=300A/μs		11.2	15	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =8.8A, di/dt=300A/μs		10.5		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

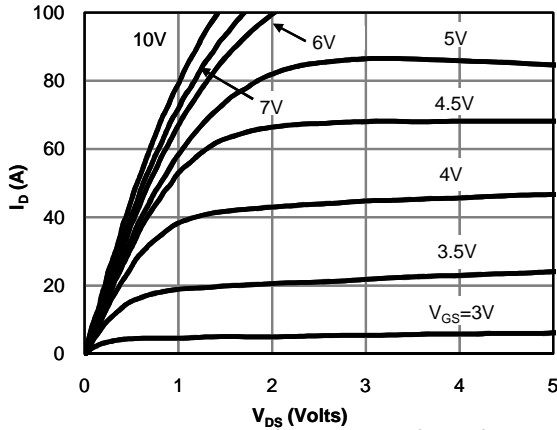
D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

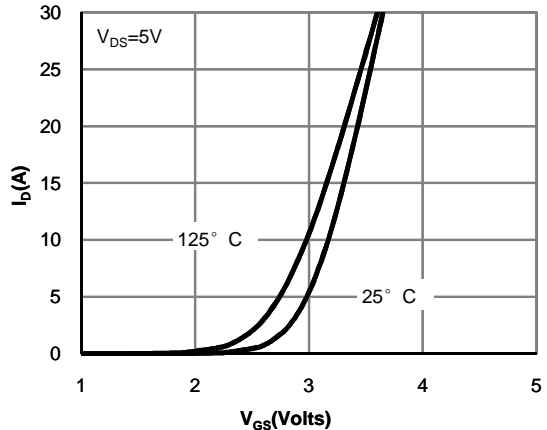
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

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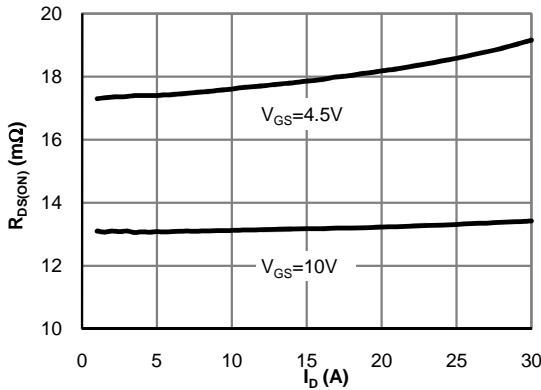
**FET1: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



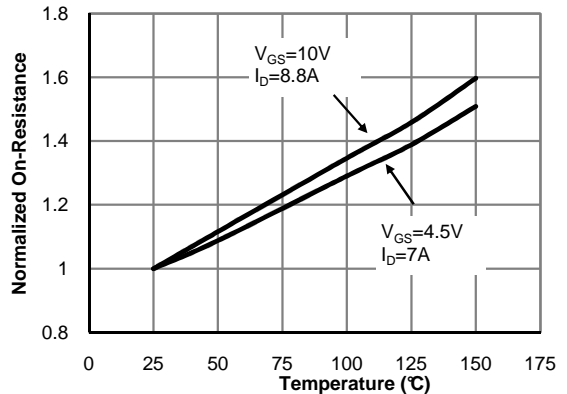
**Figure 1: On-Region Characteristics (Note E)**



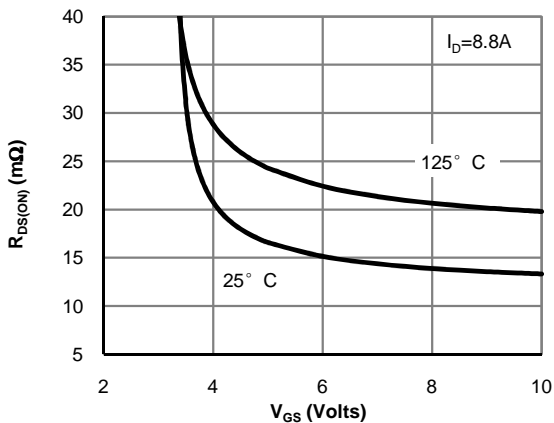
**Figure 2: Transfer Characteristics (Note E)**



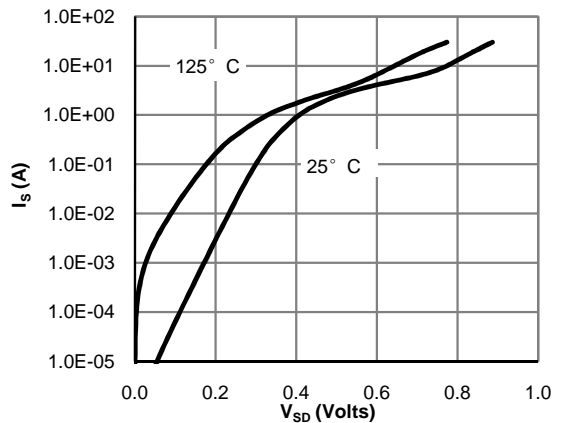
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**



**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**



**Figure 6: Body-Diode Characteristics (Note E)**

**FET1: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

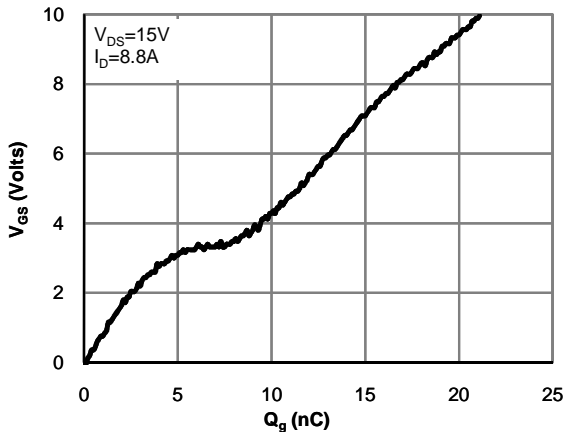


Figure 7: Gate-Charge Characteristics

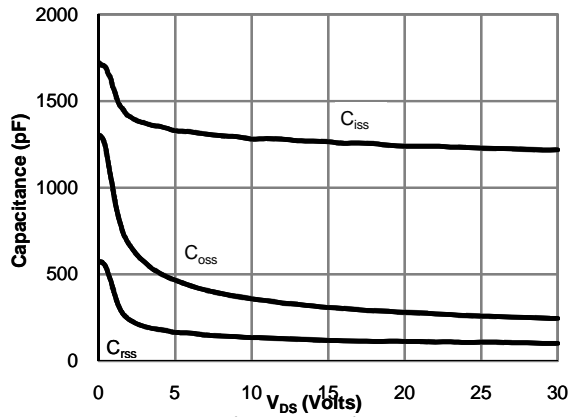


Figure 8: Capacitance Characteristics

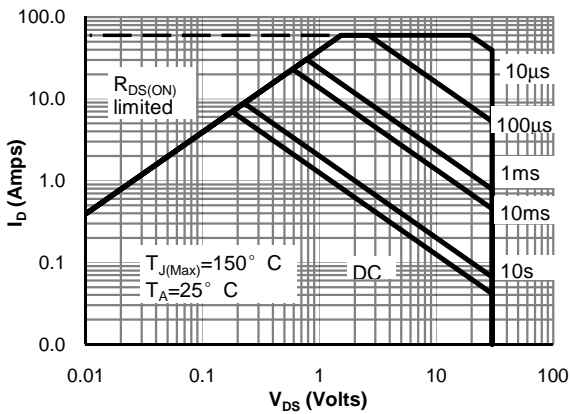


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

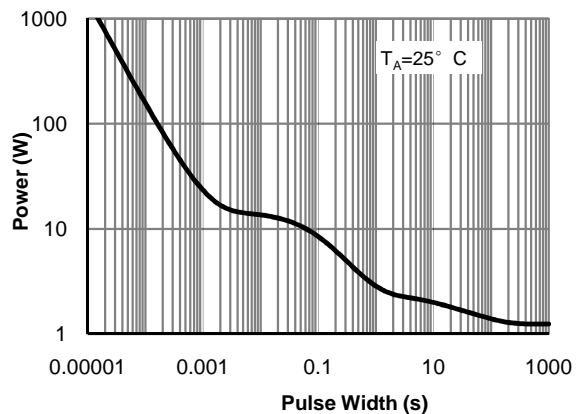


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

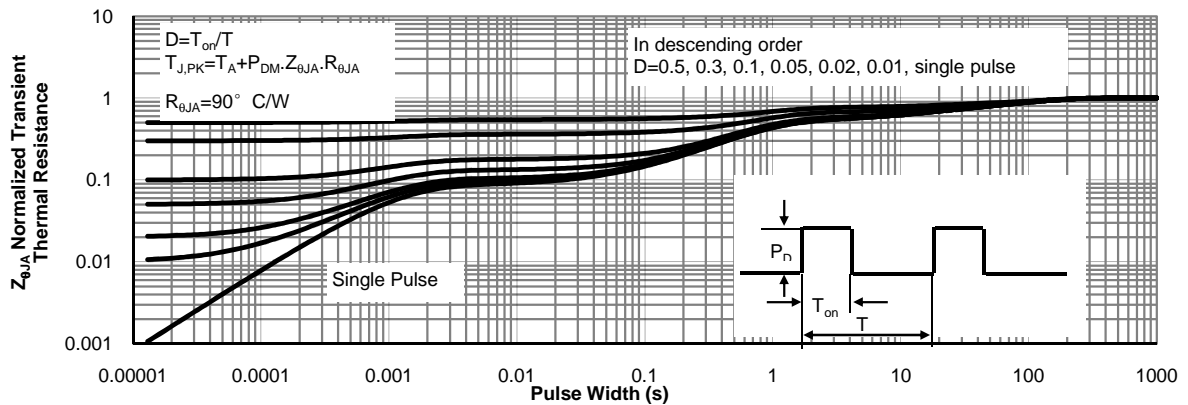


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

**FET2 Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±16V			10	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	1.2	1.8	2.4	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	40			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =8A T <sub>J</sub> =125°C		15.5 21	19 25	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		18.6	28	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =8A		30		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.75	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz	600	740	888	pF
C <sub>oss</sub>	Output Capacitance		77	110	145	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		50	82	115	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	0.5	1.1	1.7	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =8A	12	15	18	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge		6	7.5	9	nC
Q <sub>gs</sub>	Gate Source Charge		2	2.5	3	nC
Q <sub>gd</sub>	Gate Drain Charge		2	3	5	nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.8Ω, R <sub>GEN</sub> =3Ω		5		ns
t <sub>r</sub>	Turn-On Rise Time			3.5		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			19		ns
t <sub>f</sub>	Turn-Off Fall Time			3.5		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =8A, dI/dt=500A/μs	6	8	10	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =8A, dI/dt=500A/μs	14	18	22	nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using ≤ 10s junction-to-ambient thermal resistance.

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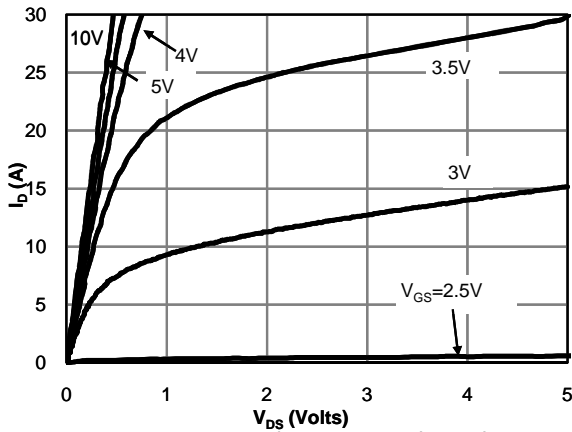
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E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

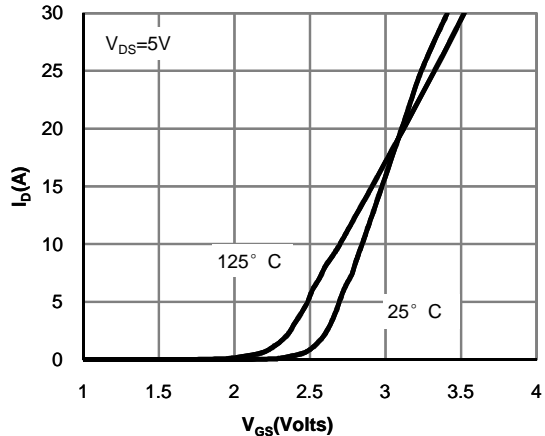
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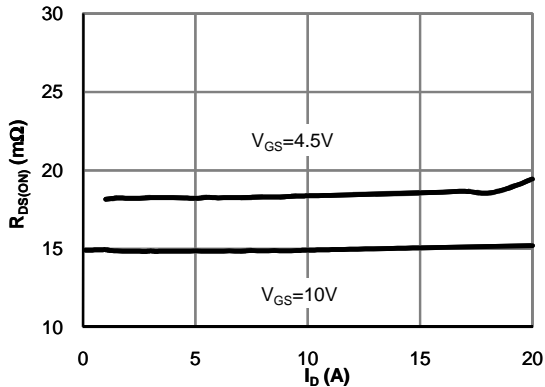
**FET2: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



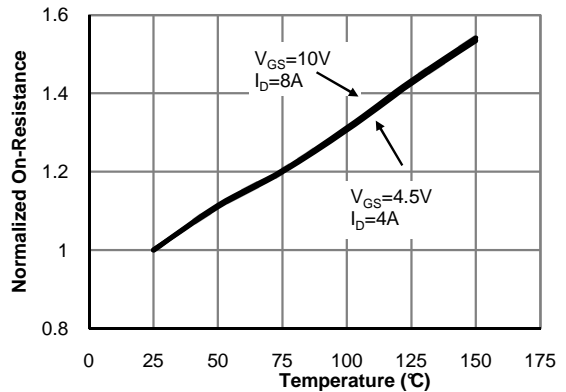
**Figure 1: On-Region Characteristics (Note E)**



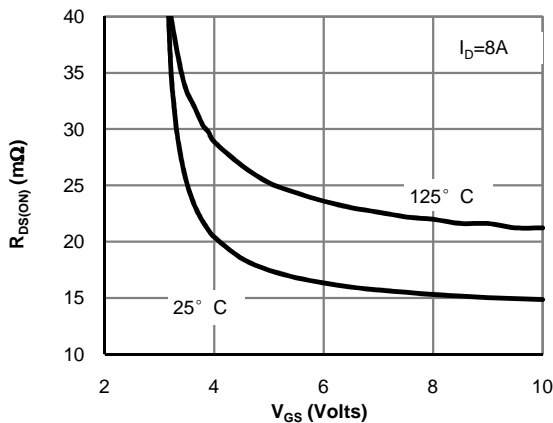
**Figure 2: Transfer Characteristics (Note E)**



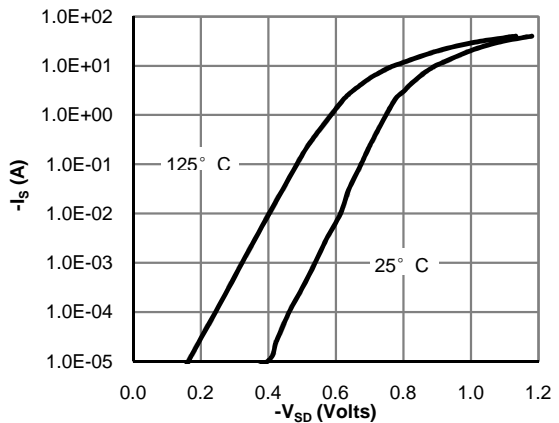
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**



**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**



**Figure 6: Body-Diode Characteristics (Note E)**

**FET2: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

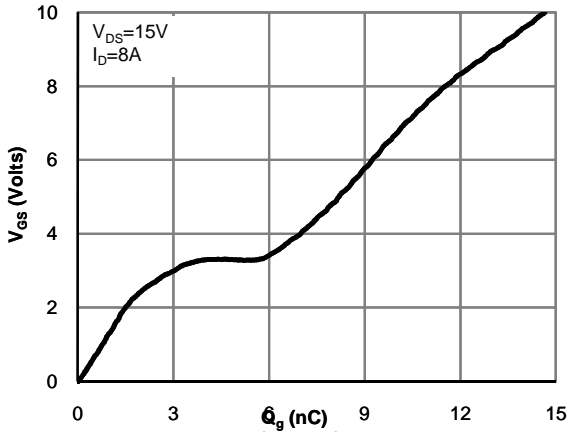


Figure 7: Gate-Charge Characteristics

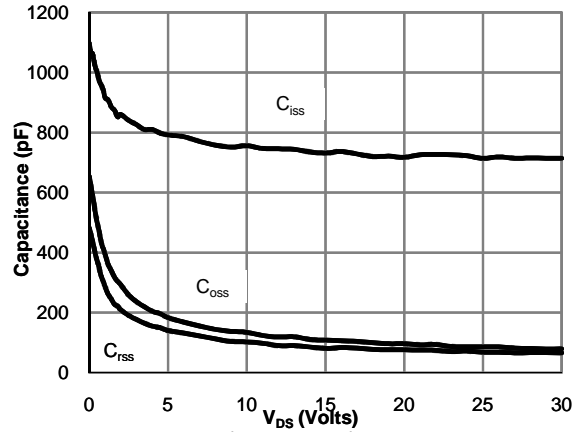


Figure 8: Capacitance Characteristics

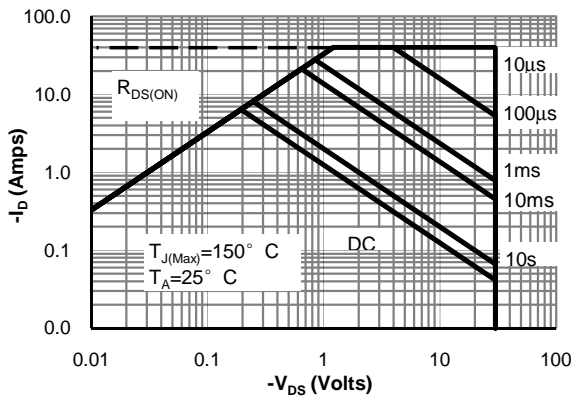


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

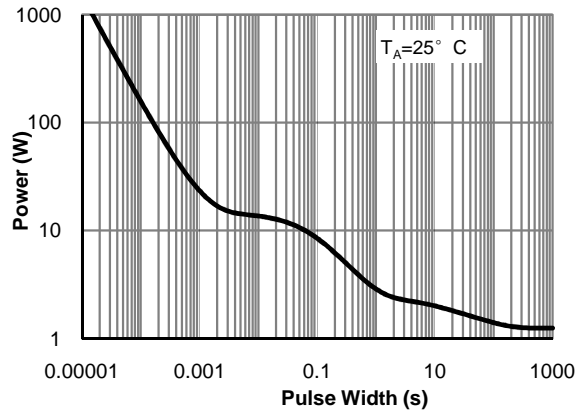


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

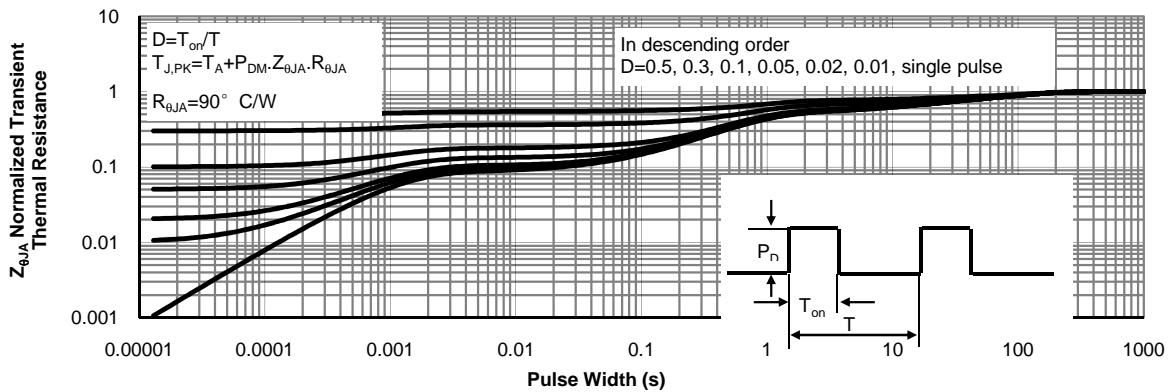
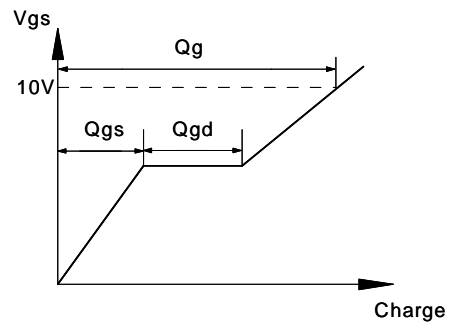
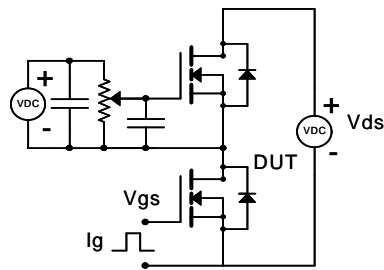
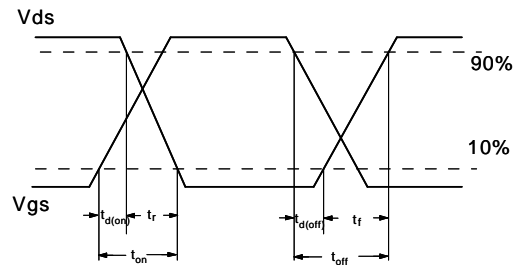
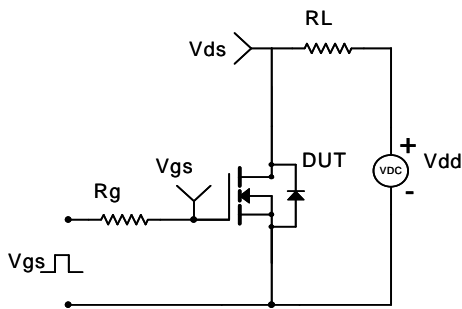


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

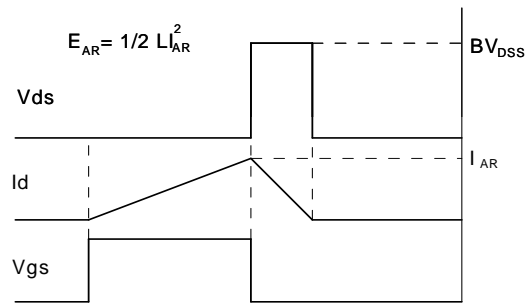
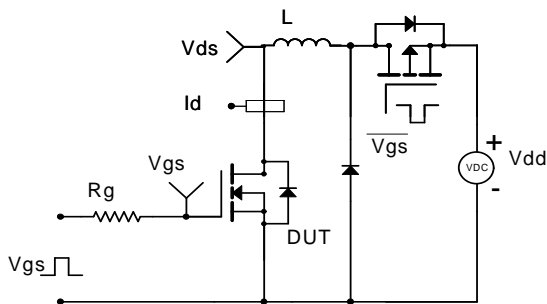
**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**

